



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	60A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	8.6 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	13 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split gate trench MOSFET technology
 Excellent package for heat dissipation
 High density cell design for low $R_{DS(ON)}$
 Moisture Sensitivity Level 1
 Epoxy Meets UL 94 V-0 Flammability Rating
 Halogen Free

Applications

High Frequency Switching
 Synchronous Rectification

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-source Voltage	V_{DS}	100	V	
Gate-source Voltage	V_{GS}	± 20	V	
Drain Current	I_D	$T_C=25$	60	A
		$T_C=100$	38	
Pulsed Drain Current ^A	I_{DM}	240	A	
Avalanche energy ^B	EAS	200	mJ	
Total Power Dissipation ^C	P_D	$T_C=25$	88	W
		$T_C=100$	35.2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 +150		

Thermal resistance

Parameter	Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	R	15	20	/W
Thermal Resistance Junction-to-Ambient ^D		40	50	



YJG60G10B

RECOMMEND
YJG60G10C
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ
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Typical Performance Characteristics

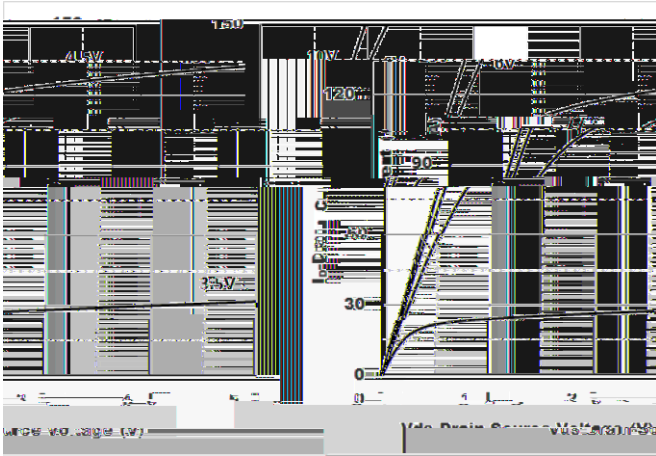


Figure1. Output Characteristics

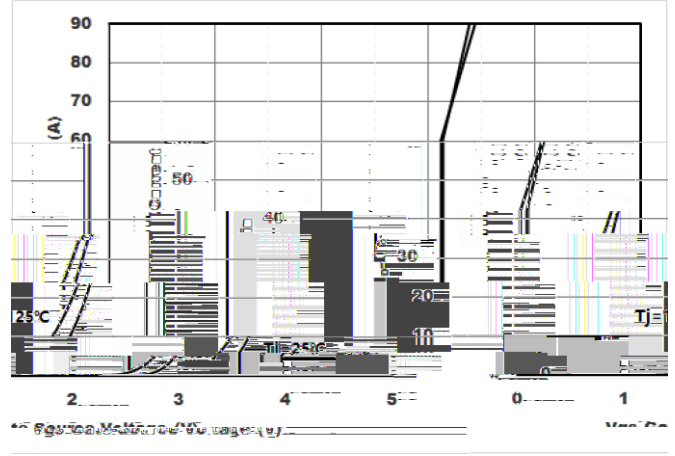


Figure2. Transfer Characteristics

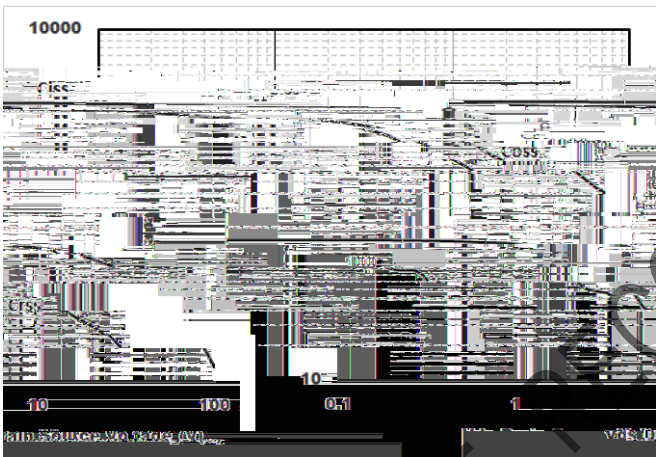


Figure3. Capacitance Characteristics

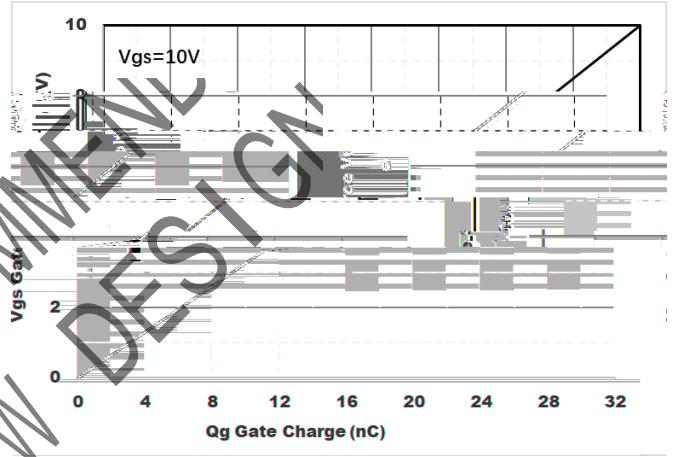


Figure4. Gate Charge

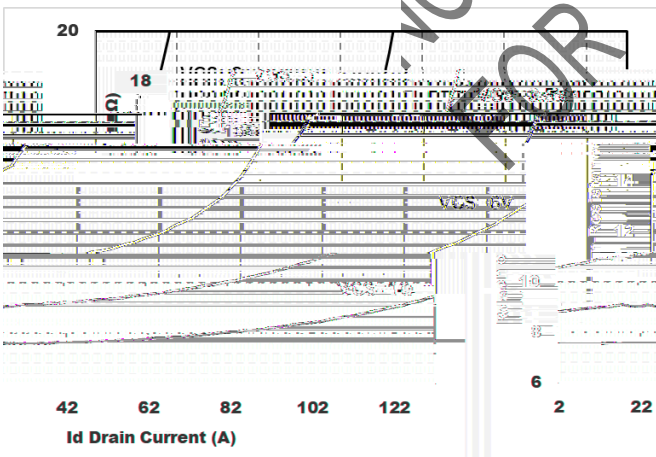


Figure5. : On-Resistance vs. Gate to Source Voltage

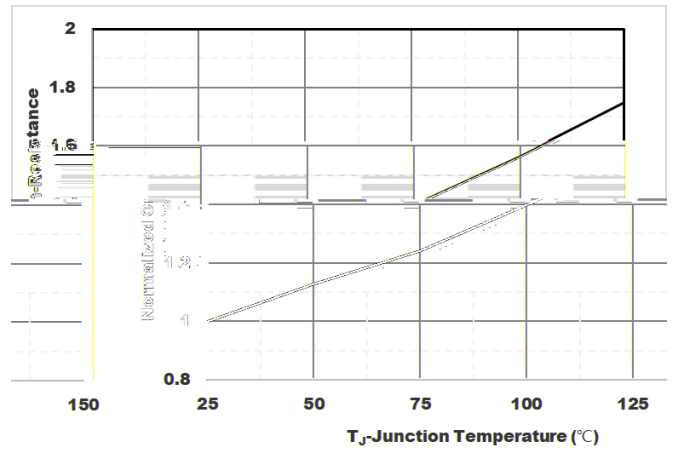


Figure6. Normalized On-Resistance

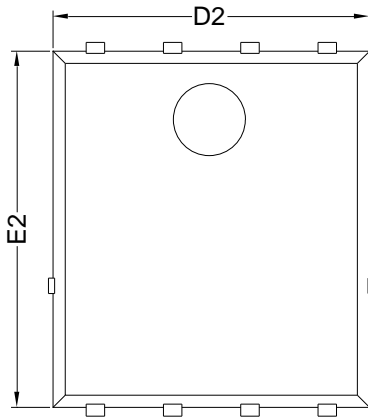


Figure7. Drain current

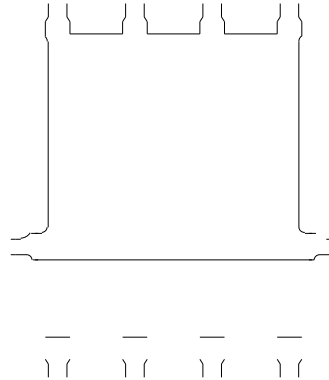
Figure8.Safe Operation Area



PDFN5060-8L-B-1.1MM Package information



Top View



Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



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